

20V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)}$	I_D $T_A = 25^\circ C$
-20V	600m Ω @ $V_{GS} = -4.5V$	-0.92A
	900m Ω @ $V_{GS} = -2.7V$	-0.75A

Description and Applications

This MOSFET utilizes a unique structure that combines the benefits of low on-resistance with fast switching speed, making it ideal for high-efficiency power management applications.

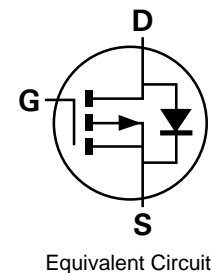
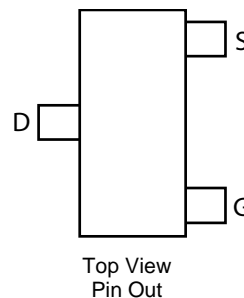
- DC - DC converters
- Power management functions
- Disconnect switches
- Motor control

Features and Benefits

- Fast switching speed
- Low on-resistance
- Low threshold
- Low gate drive
- **"Lead Free", RoHS Compliant (Note 1)**
- **Halogen and Antimony Free. "Green" Device (Note 2)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish; Solderable per MIL-STD-202, Method 208
- Weight: 0.008 grams (approximate)

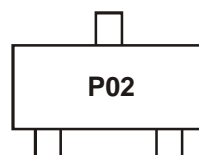


Ordering Information (Note 3)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXM61P02FTA	P02	7	8	3000 Units

- Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. No purposely added lead. Halogen and Antimony free.
 2. Diodes Inc's "Green" Policy can be found on our website at <http://www.twtysemi.com>
 3. For packaging details, go to our website at <http://www.twtysemi.com>

Marking Information



P02 = Product Type Marking Code

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	-20	V
Gate-Source Voltage			V _{GS}	±12	V
Continuous Drain Current	V _{GS} = 4.5V	T _A = 25°C (Note 5) T _A = 70°C (Note 5)	I _D	-0.9 -0.7	A
Pulsed Drain Current (Note 6)			I _{DM}	-4.9	A
Continuous Source Current (Body Diode) (Note 5)			I _S	-0.9	A
Pulsed Source Current (Body Diode) (Note 6)			I _{SM}	-4.9	A

Thermal Characteristics @T_A = 25°C unless otherwise specified

Characteristic		Symbol	Value	Unit
Power Dissipation (Note 4)		P _D	625	mW
Linear Derating Factor			5	mW/°C
Power Dissipation (Note 5)		P _D	806	mW
Linear Derating Factor			6.4	mW/°C
Thermal Resistance, Junction to Ambient (Note 4)		R _{θJA}	200	°C/W
Thermal Resistance, Junction to Ambient (Note 5)		R _{θJA}	155	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

- Notes:
4. For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions
 5. For a device surface mounted on FR4 PCB measured at t ≤ 5 secs.
 6. Repetitive rating 25mm x 25mm FR4 PCB, D=0.05 pulse width=10μs - pulse current limited by maximum junction temperature.

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	-20	—	—	V	I _D = -250μA, V _{GS} = 0V
Zero Gate Voltage Drain Current	I _{DSS}	—	—	-0.1	μA	V _{DS} = -20V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±12V, V _{DS} = 0V
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(th)}	-0.7	—	—	V	I _D = -250μA, V _{DS} = V _{GS}
Static Drain-Source On-Resistance (Note 7)	R _{DS(on)}	—	—	0.6	Ω	V _{GS} = -4.5V, I _D = -0.61A
				0.9		V _{GS} = -2.7V, I _D = -0.31A
Forward Transconductance (Notes 7 and 9)	g _{fs}	0.56	—	—	S	V _{DS} = -10V, I _D = -0.31A
Diode Forward Voltage (Note 7)	V _{SD}	—	—	-0.95	V	T _J = 25°C, I _S = -0.61A, V _{GS} = 0V
Reverse Recovery Time (Note 9)	t _{rr}	—	14.9	—	ns	T _J = 25°C, I _F = -0.61A,
Reverse Recovery Charge (Note 9)	Q _{rr}	—	5.6	—	nC	di/dt = 100A/μs
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{iss}	—	150	—	pF	V _{DS} = -15V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	—	70	—		
Reverse Transfer Capacitance	C _{rss}	—	30	—		
Turn-On Delay Time (Note 8)	t _{d(on)}	—	2.9	—	ns	V _{DD} = -110V, I _D = -0.93A, R _G ≅ 6.2Ω, R _D ≅ 11Ω,
Turn-On Rise Time (Note 8)	t _r	—	6.7	—		
Turn-Off Delay Time (Note 8)	t _{d(off)}	—	11.2	—		
Turn-Off Fall Time (Note 8)	t _f	—	10.1	—		
Total Gate Charge (Note 8)	Q _g	—	3.5	—	nC	V _{DS} = -16V, V _{GS} = -4.5V, I _D = -0.61A
Gate-Source Charge (Note 8)	Q _{gs}	—	0.5	—		
Gate-Drain Charge (Note 8)	Q _{gd}	—	1.5	—		

- Notes:
7. Measured under pulsed conditions. Pulse width = 300μs. Duty cycle ≤ 2%.
 8. Switching characteristics are independent of operating junction temperature.
 9. For design aid only, not subject to production testing.